

Power Transistor (-80V, -4A)

2SA1635

●Features

- 1) Low $V_{CE(\text{sat})}$. (Typ. -0.3V at $I_C/I_B = -2/-0.2A$)
- 2) Excellent DC current gain characteristics.
- 3) $P_c = 30W$ ($T_c = 25^\circ\text{C}$)
- 4) Wide SOA (safe operating area).
- 5) Complements the 2SC4008.

●Packaging specifications and hFE

Type	2SA1635
Package	TO-220FP
hFE	E
Code	-
Basic ordering unit (pieces)	500

●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	-80	V
Collector-emitter voltage	V_{CEO}	-80	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-4	A
Collector power dissipation	P_c	30	W ($T_c = 25^\circ\text{C}$)
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~150	°C

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-80	—	—	V	$I_C = -1\text{mA}$
Collector-emitter breakdown voltage	BV_{CEO}	-80	—	—	V	$I_C = -50\text{\mu A}$
Emitter-base breakdown voltage	BV_{EBO}	-5	—	—	V	$I_E = -50\text{\mu A}$
Collector cutoff current	I_{CEO}	—	—	-10	\mu A	$V_{CE} = -80V$
Emitter cutoff current	I_{EBO}	—	—	-10	\mu A	$V_{EB} = -4V$
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	—	—	-1.5	V	$I_C/I_B = -2A/-0.2A$
Base-emitter saturation voltage	$V_{BE(\text{sat})}$	—	—	-1.5	V	$I_C/I_B = -2A/-0.2A$
DC current transfer ratio	h_{FE}	100	—	200	—	$V_{CE}/I_C = -4V/-1A$
Transition frequency	f_T	—	12	—	MHz	$V_{CE} = -12V, I_C = 0.5A$
Output capacitance	C_{ob}	—	80	—	pF	$V_{CE} = -10V, I_C = 0A, f = 1\text{MHz}$

(90-173-B97)

Power Transistor (80V, 4A)

2SC4008

●Features

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- 2) Excellent DC current gain characteristics.
- 3) $P_c = 30W$ ($T_c = 25^\circ\text{C}$)
- 4) Wide SOA (safe operating area).
- 5) Complements the 2SA1635.

●Packaging specifications and hFE

Type	2SC4008
Package	TO-220FP
hFE	EFG
Code	—
Basic ordering unit (pieces)	500

●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limit	Unit
Collector-base voltage	V_{CBO}	100	V
Collector-emitter voltage	V_{CEO}	80	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	4	A (DC)
		6	A (Pulse) *
Collector power dissipation	P_c	2	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~150	°C

* Single pulse $P_w = 100\text{ms}$

Bi-polar transistors

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	100	—	—	V	$I_C = 50\text{\mu A}$
Collector-emitter breakdown voltage	BV_{CEO}	80	—	—	V	$I_C = 25\text{mA}$
Emitter-base breakdown voltage	BV_{EBO}	6	—	—	V	$I_E = 50\text{\mu A}$
Collector cutoff current	I_{CEO}	—	—	10	\mu A	$V_{CE} = 100V$
Emitter cutoff current	I_{EBO}	—	—	10	\mu A	$V_{EB} = 6V$
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	—	—	1	V	$I_C/I_B = 2A/0.2A$ *
Base-emitter saturation voltage	$V_{BE(\text{sat})}$	—	—	1.5	V	$I_C/I_B = 2A/0.2A$ *
DC current transfer ratio	h_{FE}	100	—	500	—	$V_{CE}/I_C = 4V/1A$
Transition frequency	f_T	—	10	—	MHz	$V_{CE} = 12V, I_C = -0.2A, f = 5\text{MHz}$ *
Output capacitance	C_{ob}	—	60	—	pF	$V_{CE} = 10V, I_C = 0A, f = 1\text{MHz}$

* Measured using pulse current.

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275

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